

Silicon NPN Power Transistors

2SC1162

DESCRIPTION

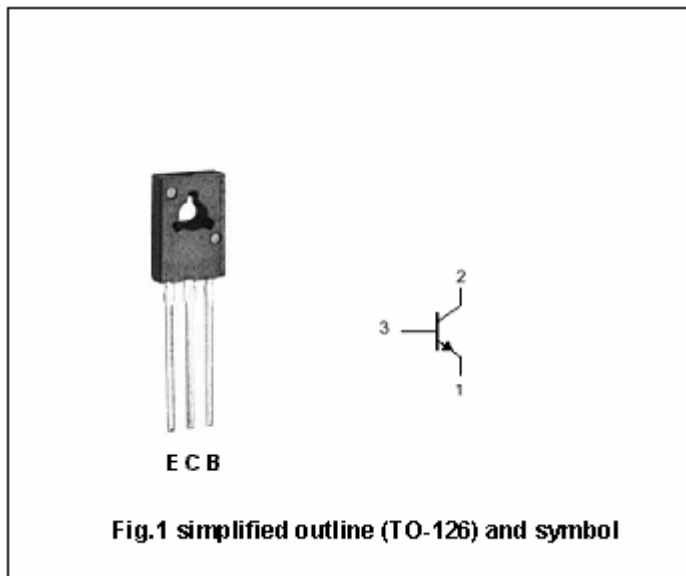
- With TO-126 package
- Complement to type 2SA715

APPLICATIONS

- For low frequency power amplifier applications

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector;connected to mounting base
3	Base



Absolute Maximun Ratings (Ta=25 )

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$V_{CBO}$	Collector-base voltage	Open emitter	35	V
$V_{CEO}$	Collector-emitter voltage	Open base	35	V
$V_{EBO}$	Emitter-base voltage	Open collector	5	V
$I_C$	Collector current (DC)		2.5	A
$I_{CM}$	Collector current-peak		3	A
$P_C$	Collector power dissipation	$T_a=25$	0.75	W
		$T_C=25$	10	
$T_j$	Junction temperature		150	
$T_{stg}$	Storage temperature		-55~150	

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## CHARACTERISTICS

T<sub>j</sub>=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-emitter breakdown voltage	I <sub>C</sub> =10mA I <sub>B</sub> =0	35			V
V <sub>(BR)CBO</sub>	Collector-base breakdown voltage	I <sub>C</sub> =1mA ; I <sub>E</sub> =0	35			V
V <sub>(BR)EBO</sub>	Emitter-base breakdown voltage	I <sub>E</sub> =1mA ; I <sub>C</sub> =0	5			V
V <sub>CEsat</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =2.0A ; I <sub>B</sub> =0.2A(Pulse test)			1.0	V
V <sub>BE</sub>	Base-emitter on voltage	I <sub>C</sub> =1.5A ; V <sub>CE</sub> =2V(Pulse test)			1.5	V
I <sub>CBO</sub>	Collector cut-off current	V <sub>CB</sub> =35V ; I <sub>E</sub> =0			20	μ A
I <sub>EBO</sub>	Emitter cut-off current	V <sub>EB</sub> =3V ; I <sub>C</sub> =0			1	μ A
h <sub>FE-1</sub>	DC current gain	I <sub>C</sub> =0.5A ; V <sub>CE</sub> =2V	60		320	
h <sub>FE-2</sub>	DC current gain	I <sub>C</sub> =1.5A ; V <sub>CE</sub> =2V(Pulse test)	20			
f <sub>T</sub>	Transition frequency	I <sub>C</sub> =0.2A ; V <sub>CE</sub> =2V(Pulse test)		180		MHz

◆ h<sub>FE-1</sub> Classifications

B	C	D
60-120	100-200	160-320

PACKAGE OUTLINE

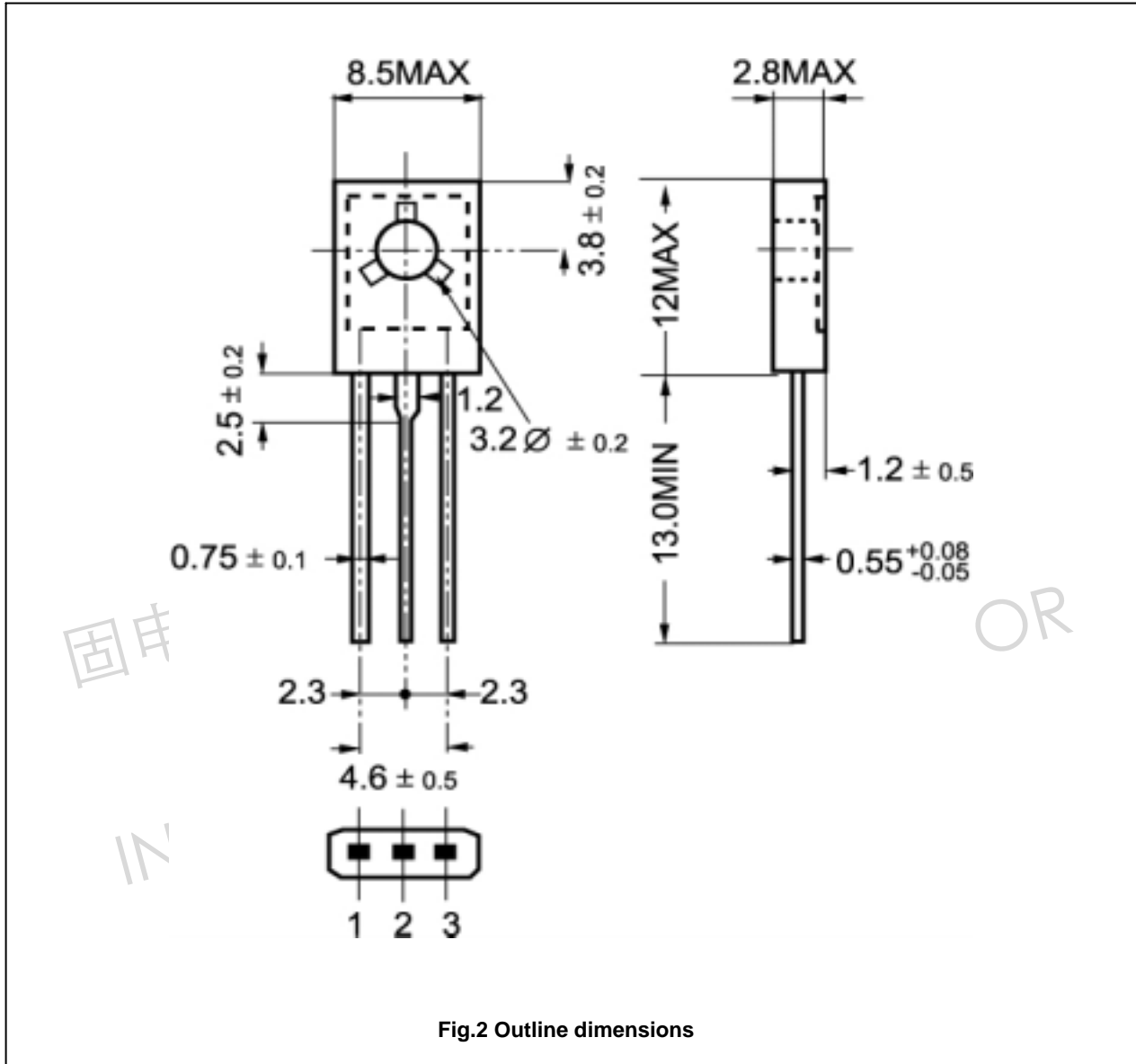


Fig.2 Outline dimensions

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